



Product data sheet

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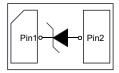


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DFN1610-2L



Circuit diagram

Marking H12N

Feature

- 1600W Peak pulse power per line (t_P = 8/20µs)
- DFN1610-2L package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- Low clamping Voltage
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD)
 ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

Applications

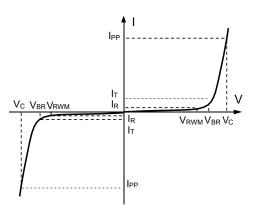
- > Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- > Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

Mechanical Characteristics

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- > Qualified max reflow temperature:260°C
- Pure tin plating: 7 ~ 17 um
- ➢ Pin flatness:≤3mil
- > Device meets MSL3 requirements

Electronics Parameter

Symbol	Parameter	
VRWM	Peak Reverse Working Voltage	
IR	Reverse Leakage Current @ V _{RWM}	
V _{BR}	Breakdown Voltage @ I⊤	
Ιτ	Test Current	
IPP	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
P _{PP}	Peak Pulse Power	
Сл	Junction Capacitance	







Electrical characteristics per line@25°C(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}				12	V
Breakdown Voltage	V _{BR}	It=1mA	13.5	15.0		V
Reverse Leakage Current	I _R	V _{RWM} =12V			1	μA
Clamping Voltage	Vc	I _{PP} =65A t _P = 8/20µs		30.0	35.0	V
Junction Capacitance	Cj	V _R =0V f = 1MHz	300	355	400	pF

Absolute maximum rating@25℃

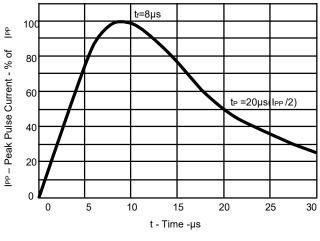
Rating	Symbol	Value	Units
Peak Pulse Power ($t_P = 8/20\mu S$)	P _{pp}	1600	W
Lead Soldering Temperature	T∟	260 (10 sec)	°C
Operating Temperature	TJ	-55 to +125	°C
Storage Temperature	T _{STG}	-55 to +150	°C

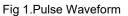


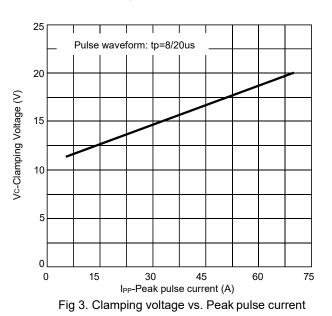
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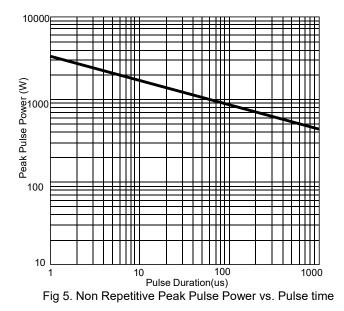
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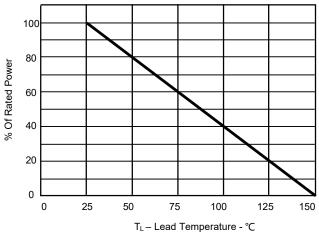
Typical Characteristics



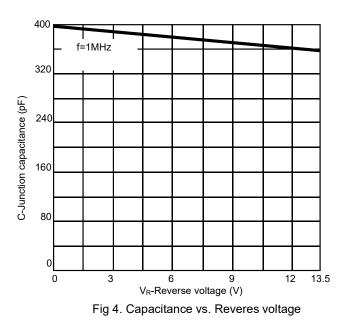










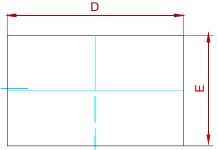


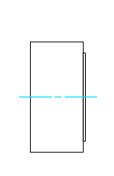


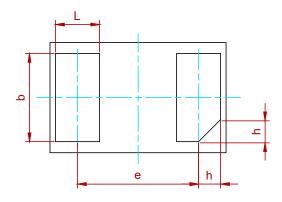
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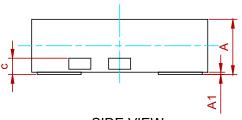
PACKAGE MECHANICAL DATA







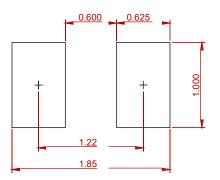
TOP VIEW



BOTTOM VIEW

Symbol	Dimensions in Millimeters			
	Min.	Тур.	Max.	
А	0.45	0.50	0.55	
A1	0.00	0.02	0.05	
с	0.15 Ref.			
b	0.75	0.80	0.85	
L	0.35	0.40	0.45	
D	1.55	1.60	1.65	
E	0.95	1.00	1.05	
e	1.10 BSC			
h	0.20 Ref.			

Recommend PCB Layout (Unit: mm)



Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.

REEL SPECIFICATION

P/N	PKG	QTY
PTVSHC2EN12VU-MS	DFN1610-2L	3000



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